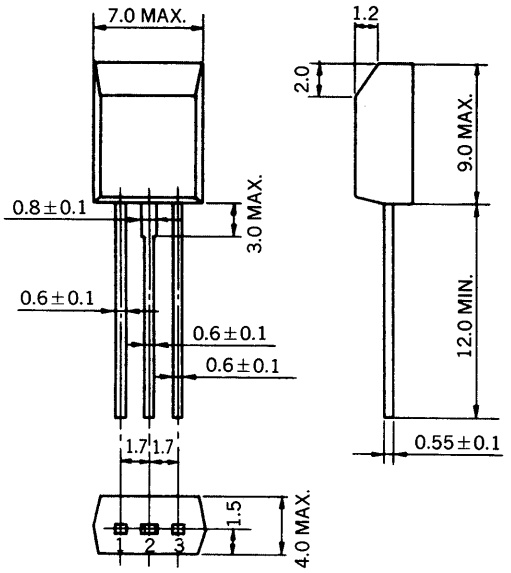
MOS FIELD EFFECT TRANSISTOR

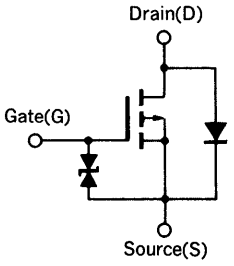
2SJ180

P-CHANNEL MOS FET
FOR HIGH-SPEED SWITCHING

OUTLINE DIMENSIONS (Unit : mm)



1. Gate
2. Drain
3. Source



(Diode in the figure is the parasitic diode.)

The 2SJ180, P-channel vertical type MOS FET, is a switching device which can be driven directly by the output of ICs having a 5 V power source.

As the MOS FET has low on-state resistance and excellent switching characteristics, it is suitable for driving actuators such as motors, relays, and solenoids.

FEATURES

- Directly driven by ICs having a 5 V power supply.
- Has low on-state resistance
  $R_{DS(on)}$ = 1.5 Ω MAX. @V_{GS} = −4.0 V, I_D = −0.5 A
  $R_{DS(on)}$ = 1.0 Ω MAX. @V_{GS} = −10 V, I_D = −0.5 A
- Voltage drive at logic level (V_{GS} = −4 V) is possible.
- Bidirectional zener diode for protection is incorporated in between the gate and the source.
- Inductive loads can be driven without protective circuit thanks to the improved breakdown voltage between the drain and source.

QUALITY GRADE

Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS (T_a = 25 °C)

CHARACTERISTIC	SYMBOL	RATINGS	UNIT	TEST CONDITIONS
Drain to Source Voltage	V_{DSS}	−30	V	V_{GS} = 0
Gate to Source Voltage	V_{GSS}	∓20	V	V_{DS} = 0
Drain Current	$I_{D(DC)}$	∓1.0	A	
Drain Current	$I_{D(pulse)}$	∓2.0	A	PW ≦ 10 ms, Duty Cycle ≦ 50 %
Total Power Dissipation	P_T	1.0	W	
Channel Temperature	T_{ch}	150	°C	
Storage Temperature	T_{stg}	−55 to +150	°C	

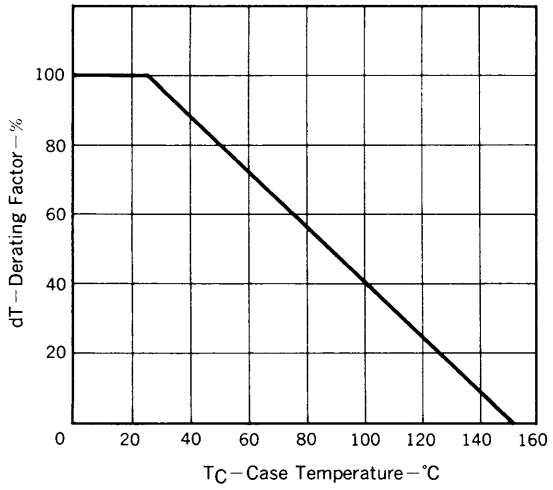
Document No. TC−2318
(O.D.No. TC−7776A)
Date Published April 1991 M
Printed in Japan

ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

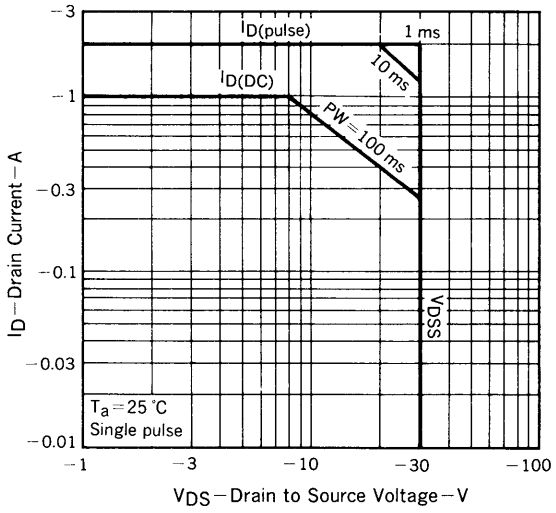
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Drain Cut-off Current	I_{DSS}			−10	μA	V_{DS} = −30 V, V_{GS} = 0
Gate Leakage Current	I_{GSS}			∓10	μA	V_{GS} = ∓20 V, V_{DS} = 0
Gate Cut-off Voltage	$V_{GS(off)}$	−1.0	−2.2	−3.0	V	V_{DS} = −10 V, I_D = −1 mA
Forward Transfer Admittance	$\|y_{fs}\|$	0.4			S	V_{DS} = −10 V, I_D = −0.5 A
Drain to Source On-State Resistance	$R_{DS(on)1}$		0.8	1.5	Ω	V_{GS} = −4.0 V, I_D = −0.5 A
Drain to Source On-State Resistance	$R_{DS(on)2}$		0.4	1.0	Ω	V_{GS} = −10 V, I_D = −0.5 A
Input Capacitance	C_{iss}		160		pF	V_{DS} = −10 V, V_{GS} = 0, f = 1 MHz
Output Capacitance	C_{oss}		130		pF	
Feedback Capacitance	C_{rss}		3		pF	
Turn-On Delay Time	$t_{d(on)}$		130		ns	$V_{GS(on)}$ = −4 V, R_G = 10 Ω, V_{DD} = −5 V, I_D = −0.3 A, R_L = 1.5 Ω
Rise Time	t_r		380		ns	
Turn-Off Delay Time	$t_{d(off)}$		95		ns	
Fall Time	t_f		140		ns	

TYPICAL CHARACTERISTICS (T_a = 25 °C)

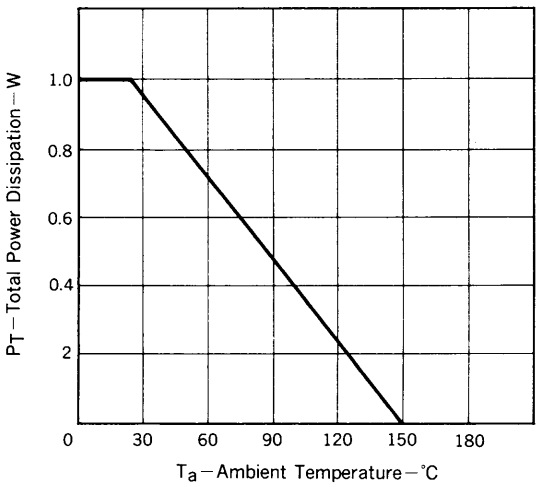
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



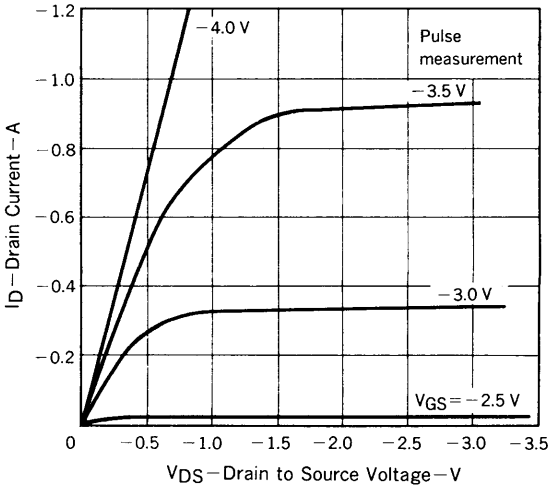
FORWARD BIAS SAFE OPERATING AREA



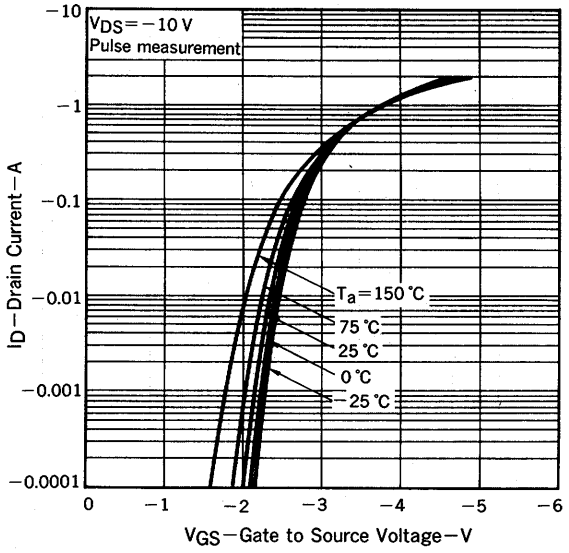
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



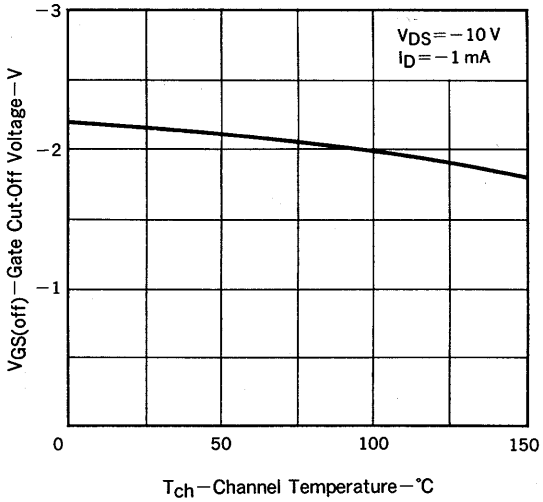
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



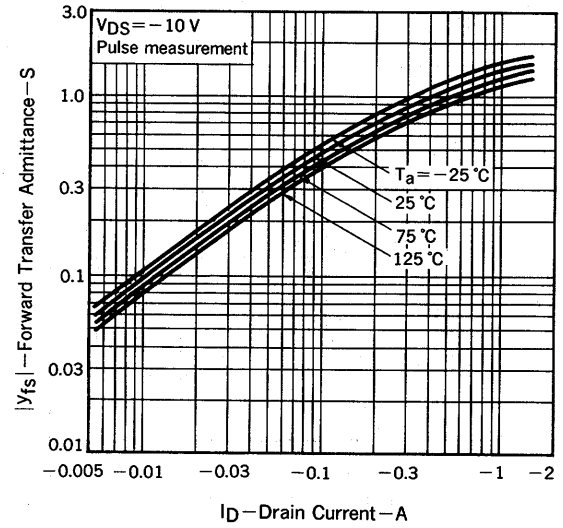
TRANSFER CHARACTERISTICS



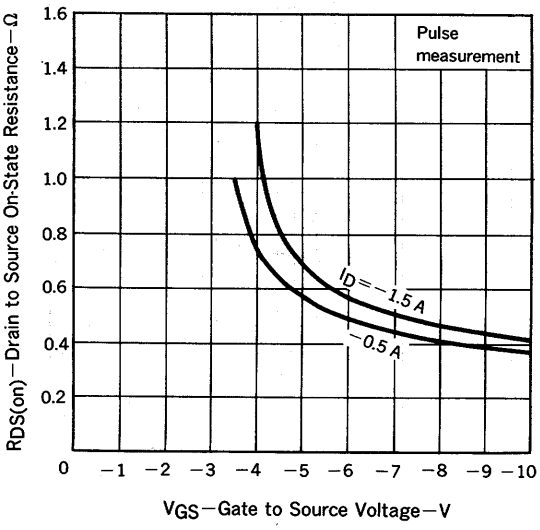
GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE



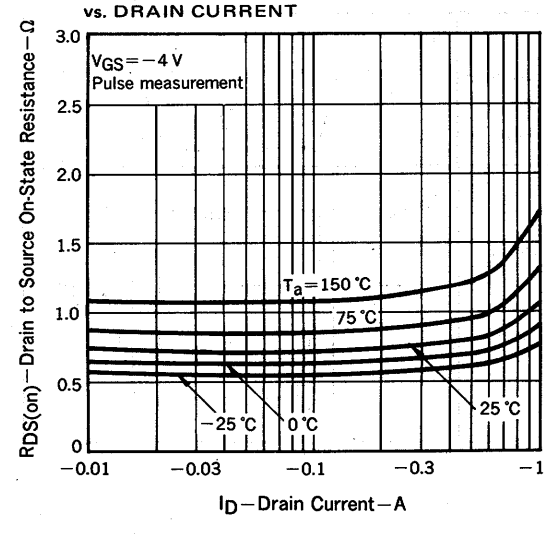
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



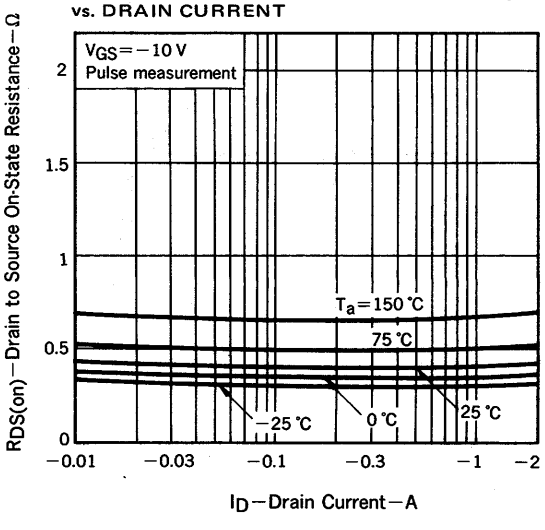
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



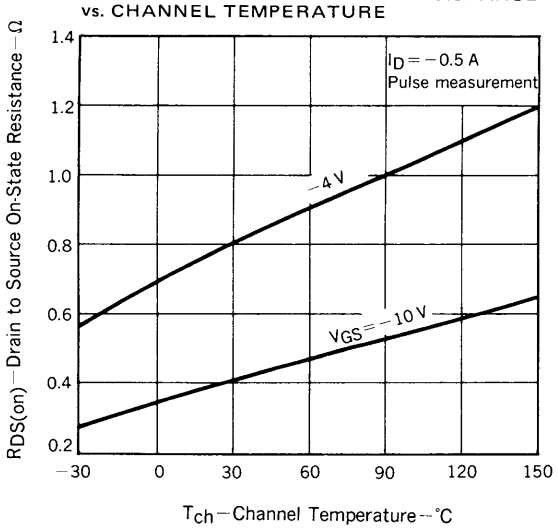
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



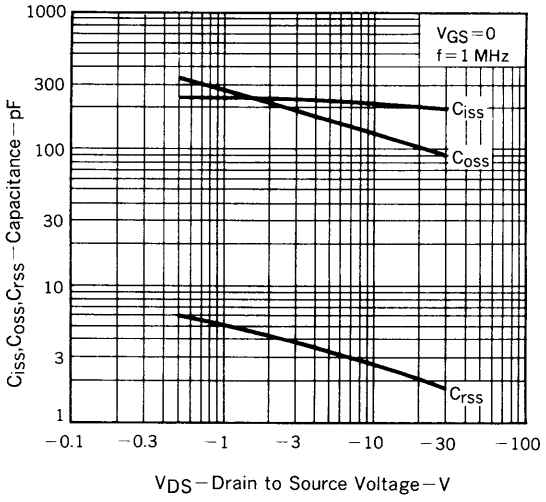
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



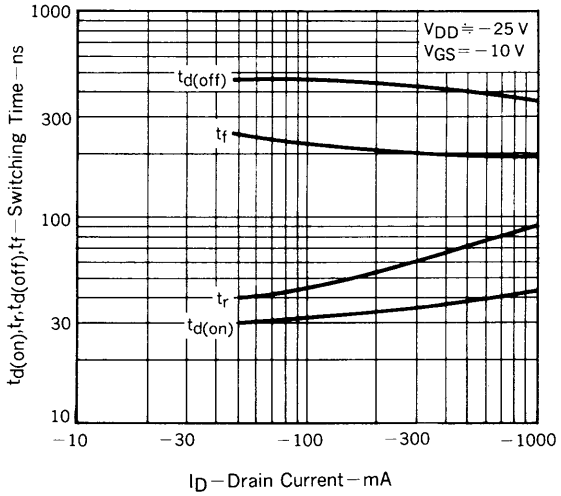
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



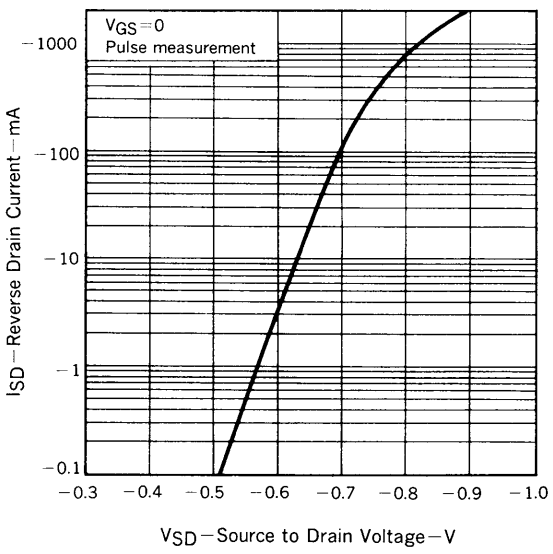
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



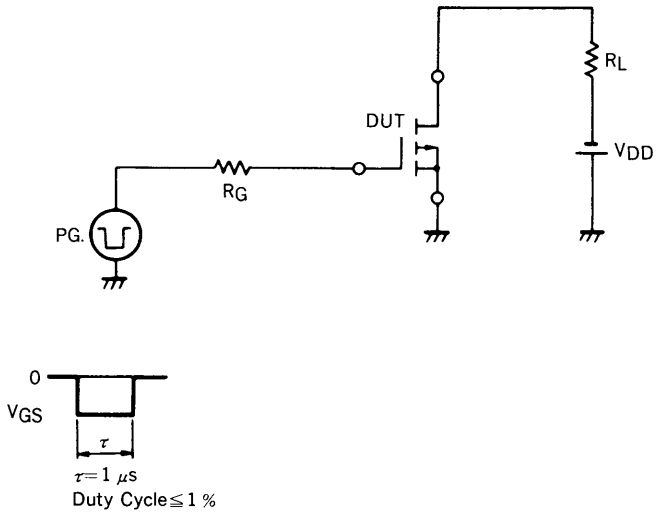
SWITCHING CHARACTERISTICS

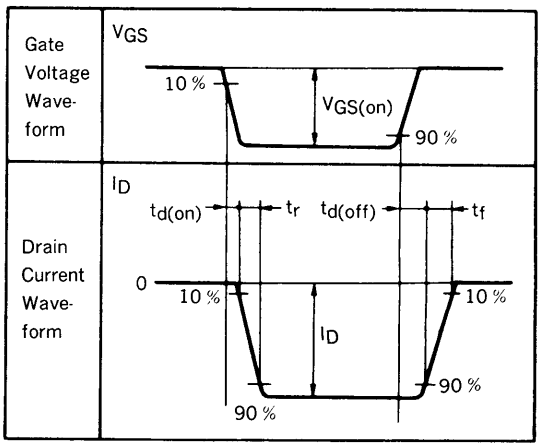


SOURCE TO DRAIN DIODE FORWARD VOLTAGE



SWITCHING TIME MEASUREMENT CIRCUIT AND CONDITIONS





RECOMMENDED SOLDERING CONDITIONS

Solder this product under the following recommended conditions.
For soldering methods or soldering conditions other than those recommended in the table, please consult our NEC salespeople.

Insert type

Soldering method	Soldering conditions	Recommended condition code
Wave soldering	Solder bath temperature: 260 °C max. Soldering time: 10 sec max.	

[MEMO]